

RJK5015DPM

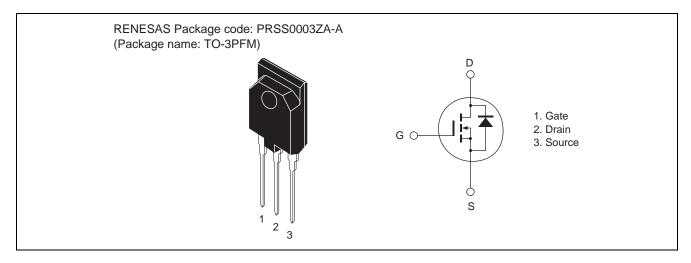
Silicon N Channel MOS FET High Speed Power Switching

REJ03G1753-0100 Rev.1.00 Oct 26, 2009

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	500	V
Gate to source voltage	V_{GSS}	±30	V
Drain current	I _D Note4	25	А
Drain peak current	I _{D (pulse)} Note1	75	А
Body-drain diode reverse drain current	I _{DR}	25	А
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	75	А
Avalanche current	I _{AP} Note3	7	А
Avalanche energy	E _{AR} Note3	2.7	mJ
Channel dissipation	Pch Note2	60	W
Channel to case thermal impedance	θch-c	2.08	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at Tc = 25°C
- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C
- 4. Limited by maximum safe operation area

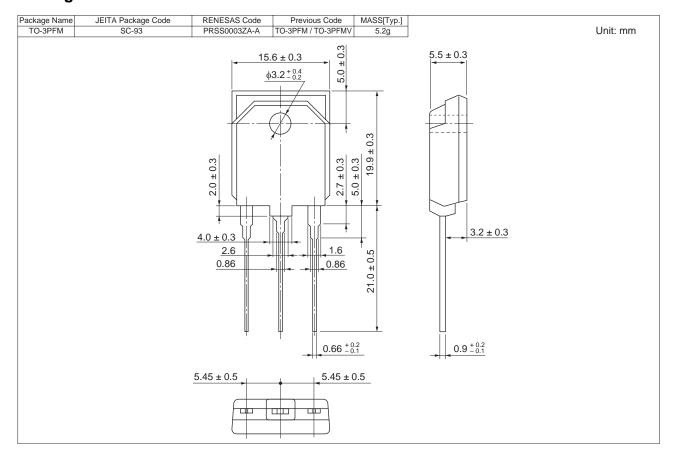
Electrical Characteristics

 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	500	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}			1	μΑ	$V_{DS} = 500 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}		_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}	_	0.21	0.24	Ω	$I_D = 12.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note5}}$
Input capacitance	Ciss		2600		pF	V _{DS} = 25 V
Output capacitance	Coss	_	270	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	32	_	pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	_	42	_	ns	I _D = 12.5 A
Rise time	t _r	_	59	_	ns	V _{GS} = 10 V
Turn-off delay time	t _{d(off)}	_	103	_	ns	$R_L = 20 \Omega$
Fall time	t _f	_	45	_	ns	$Rg = 10 \Omega$
Total gate charge	Qg	_	66	_	nC	V _{DD} = 400 V
Gate to source charge	Qgs	_	14	_	nC	V _{GS} = 10 V
Gate to drain charge	Qgd	_	29	_	nC	I _D = 25 A
Body-drain diode forward voltage	V_{DF}	_	0.96	1.60	V	$I_F = 25 \text{ A}, V_{GS} = 0^{\text{Note5}}$
Body-drain diode reverse recovery time	t _{rr}		380		ns	$I_F = 25 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 5. Pulse test

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK5015DPM-00-T1	360 pcs	Box (Tube)

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